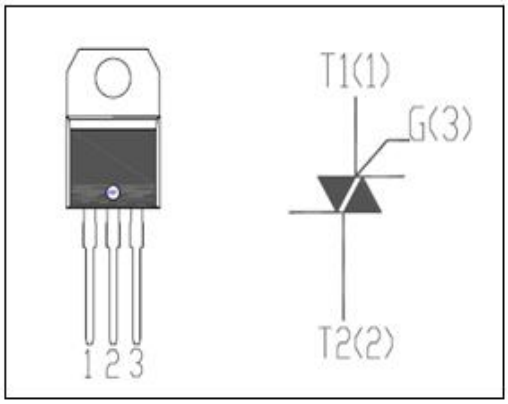
isc Thyristors BT136-800E

DESCRIPTION

- With TO-220 packaging
- Operating in 4 quadrants
- High commutation capability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Switching applications
- Phase control
- Static switching on inductive or resistive load

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER		MAX	UNIT
V_{DRM}	Repetitive peak off-state voltage		800	V
V_{RRM}	Repetitive peak reverse voltage		800	V
$I_{T(RSM)}$	Average on-state current		4	A
I_{TSM}	Surge non-repetitive on-state current	50HZ 60HZ	25 27	A
$P_{G(AV)}$	Average gate power dissipation (over any 20 ms period)		0.5	W
T_j	Operating junction temperature		-40~125	℃
T_{stg}	Storage temperature		-40~150	℃

ELECTRICAL CHARACTERISTICS (T_C=25℃ unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS		MIN	MAX	UNIT
I_{RRM}	Repetitive peak reverse current	V_R=V_{RRM} Rated; V_D=V_{DRM} Rated;	Tj=125℃		0.5	mA
I_{DRM}	Repetitive peak off-state current					
V_{TM}	On-state voltage	I_T=5A			1.7	V
I_{GT}	Gate-trigger current	V_D =12V;I_T=0.1A;	I		35	mA
			II		35	
			III		35	
			IV		70	
V_{GT}	Gate-trigger voltage	V_D =12V;I_T=0.1A;			1.5	V
Rth $_{(j\text{-}mb)}$	Junction to mounting base	Half cycle			3.7	℃/W